

CentralTM Semiconductor Corp.

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Manufacturers of World Class Discrete Semiconductors
www.centrasemi.com

2N2221A
2N2222A

NPN SILICON TRANSISTOR

JEDEC TO-18 CASE

DESCRIPTION:

The CENTRAL SEMICONDUCTOR 2N2221A, 2N2222A types are Silicon NPN Planar Epitaxial Transistors designed for small signal general purpose and switching applications.

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

	<u>SYMBOL</u>		<u>UNITS</u>
Collector-Base Voltage	V_{CB0}	75	V
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	6.0	V
Collector Current	I_C	800	mA
Power Dissipation	P_D	400	mW
Power Dissipation ($T_C=25^\circ\text{C}$)	P_D	1.2	W
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +200	$^\circ\text{C}$
Thermal Resistance	Θ_{JA}	438	$^\circ\text{C/W}$
Thermal Resistance	Θ_{JC}	146	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

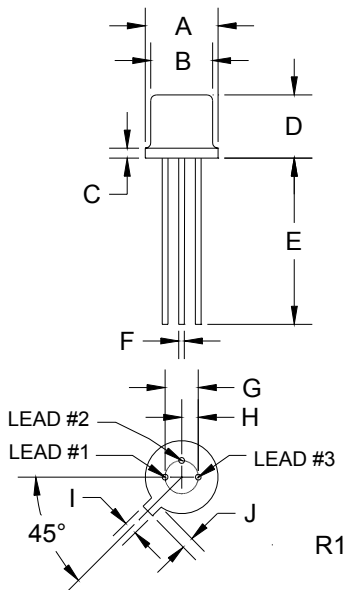
<u>SYMBOL</u>	<u>TEST CONDITIONS</u>	2N2221A		2N2222A		<u>UNITS</u>
		<u>MIN</u>	<u>MAX</u>	<u>MIN</u>	<u>MAX</u>	
I_{CBO}	$V_{CB}=60\text{V}$		10		10	nA
I_{CBO}	$V_{CB}=60\text{V}, T_A=150^\circ\text{C}$		10		10	μA
I_{EBO}	$V_{EB}=3.0\text{V}$		10		10	nA
I_{CEV}	$V_{CE}=60\text{V}, V_{EB}=3.0\text{V}$		10		10	nA
BV_{CBO}	$I_C=10\mu\text{A}$	75		75		V
BV_{CEO}	$I_C=10\text{mA}$	40		40		V
BV_{EBO}	$I_E=10\mu\text{A}$	6.0		6.0		V
$V_{CE(SAT)}$	$I_C=150\text{mA}, I_B=15\text{mA}$		0.3		0.3	V
$V_{CE(SAT)}$	$I_C=500\text{mA}, I_B=50\text{mA}$		1.0		1.0	V
$V_{BE(SAT)}$	$I_C=150\text{mA}, I_B=15\text{mA}$	0.6	1.2	0.6	1.2	V
$V_{BE(SAT)}$	$I_C=500\text{mA}, I_B=50\text{mA}$		2.0		2.0	V
h_{FE}	$V_{CE}=10\text{V}, I_C=0.1\text{mA}$	20		35		
h_{FE}	$V_{CE}=10\text{V}, I_C=1.0\text{mA}$	25		50		
h_{FE}	$V_{CE}=10\text{V}, I_C=10\text{mA}$	35		75		
h_{FE}	$V_{CE}=10\text{V}, I_C=10\text{mA}, T_A=-55^\circ\text{C}$	15		35		
h_{FE}	$V_{CE}=10\text{V}, I_C=150\text{mA}$	40	120	100	300	
h_{FE}	$V_{CE}=1.0\text{V}, I_C=150\text{mA}$	20		50		
h_{FE}	$V_{CE}=10\text{V}, I_C=500\text{mA}$	25		40		

(Continued)

ELECTRICAL CHARACTERISTICS: Continued

SYMBOL	TEST CONDITIONS	2N2221A		2N2222A		UNITS
		MIN	MAX	MIN	MAX	
f_T	$V_{CE}=20V, I_C=20mA, f=100MHz$	250		300		MHz
C_{ob}	$V_{CB}=10V, I_E=0, f=100kHz$		8.0		8.0	pF
C_{ib}	$V_{EB}=0.5V, I_C=0, f=100kHz$		25		25	pF
h_{ie}	$V_{CE}=10V, I_C=1.0mA, f=1.0kHz$	1.0	3.5	2.0	8.0	k Ω
h_{ie}	$V_{CE}=10V, I_C=10mA, f=1.0kHz$	0.2	1.0	0.25	1.25	k Ω
h_{re}	$V_{CE}=10V, I_C=1.0mA, f=1.0kHz$		5.0		8.0	$\times 10^{-4}$
h_{re}	$V_{CE}=10V, I_C=10mA, f=1.0kHz$		2.5		4.0	$\times 10^{-4}$
h_{fe}	$V_{CE}=10V, I_C=1.0mA, f=1.0kHz$	30	150	50	300	
h_{fe}	$V_{CE}=10V, I_C=10mA, f=1.0kHz$	50	300	75	375	
h_{oe}	$V_{CE}=10V, I_C=1.0mA, f=1.0kHz$	3.0	15	5.0	35	$\mu mhos$
h_{oe}	$V_{CE}=10V, I_C=10mA, f=1.0kHz$	10	100	25	200	$\mu mhos$
$rb'C_C$	$V_{CB}=10V, I_E=20mA, f=31.8MHz$		150		150	ps
NF	$V_{CE}=10V, I_C=100\mu A, R_S=1.0k\Omega, f=1.0kHz$				4.0	dB
t_d	$V_{CC}=30V, V_{BE}=0.5, I_C=150mA, I_{B1}=15mA$		10		10	ns
t_r	$V_{CC}=30V, V_{BE}=0.5, I_C=150mA, I_{B1}=15mA$		25		25	ns
t_s	$V_{CC}=30V, I_C=150mA, I_{B1}=I_{B2}=15mA$		225		225	ns
t_f	$V_{CC}=30V, I_C=150mA, I_{B1}=I_{B2}=15mA$		60		60	ns

TO-18 PACKAGE - MECHANICAL OUTLINE



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A (DIA)	0.209	0.230	5.31	5.84
B (DIA)	0.178	0.195	4.52	4.95
C	-	0.030	-	0.76
D	0.170	0.210	4.32	5.33
E	0.500	-	12.70	-
F (DIA)	0.016	0.019	0.41	0.48
G (DIA)	0.100		2.54	
H	0.050		1.27	
I	0.036	0.046	0.91	1.17
J	0.028	0.048	0.71	1.22

TO-18 (REV: R1)

LEAD CODE:

- 1) Emitter
- 2) Base
- 3) Collector

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